MPS Unbalance v140

Lennart Yseboodt, Dave van Goor, Matthias Wendt Philips Research March 5, 2015





Overview

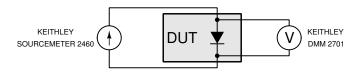
- ► Explore effect of diode forward voltage unbalance at low currents
- Temperature effect on diodes
- End to end MPS current unbalance
- Consequences for MPS design
- Proposal for MPS requirements



Measurement method

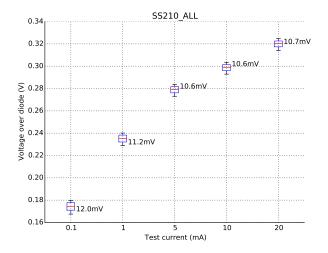
This presentation will explore measured difference in diode voltage over a number of different diodes at low current.

- Test currents: 100 μA, 1 mA, 5 mA, 10 mA, 20 mA
- Diodes: MBRM1H100, MBRM2H100, MBRS2H100, MBRS1100, MBRS1100T, MURS110, MURS210, NTSS2100ET1, NTSS2100T1, SS210, VSSA210E361T
- DUT at stable room temperature
- Total 720 measured diodes



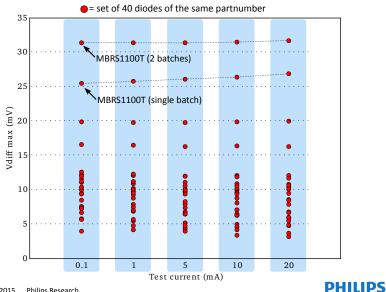


Example results



Vdiff = highest measured V_D - lowest measured V_D at test current.

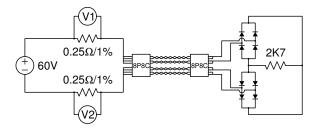
Vdiff overview



Conclusion Vdiff measurement

- Results match with match arshan_02_0115.pdf
- ► In the current range 100 µA to 20 mA the diode voltage <u>difference</u> remains constant, but <u>absolute</u> diode voltage goes up with current
- Of all measured diodes, the maximum sample to sample difference (for the same partnumber) is 32 mV
- Comparing a batch of diodes, purchased from 1 reel, to a combination of two batches (different time, different reel) increases the maximum diode voltage different by 6 mV
- Silicon or Schottky diodes exhibit the same amount of maximum voltage difference
- ... however, this is all measured at a stable constant temperature.

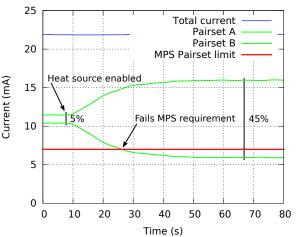
End to end MPS unbalance



- Measured pair-set current over 0.25 Ω precision resistor (resistors matched better than 1%).
- Tested with various cable lengths (1 m, 10 m)
- Diode: MBRS1100T & SS210
- ▶ Test to fail: introduce temperature difference \rightarrow can we fail MPS ?

Measurement results 1

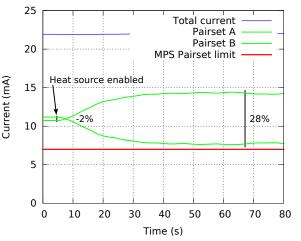
- ► I_{Port}: 22 mA
- 10 meter CAT5e
- Diode: MBRS1100T
- Vdiff(max): 34 mV
- Applied 25 °C difference between diode bridges (43 °C / 68 °C)
- Current unbalance 5% → 45%



MBRS1100T, CAT5e, 10 meter, Tdiff 25C

Measurement results 2

- ► I_{Port}: 22 mA
- 10 meter CAT5e
- ► Diode: SS210
- Vdiff(max): 10 mV
- Applied 20 °C difference between diode bridges (40 °C / 60 °C)
- Current unbalance
 -2% → 28%



SS210, CAT5e, 10 meter, Tdiff 20C

Conclusion system measurements

System end to end low current unbalance measurements show:

- ► Initial (room-temperature) low current unbalance looks good
- ► Temperature difference between diodes creates large unbalance
- ► Temperature effect is potentially far greater than intrinsic Vdiff. Temperature coefficient -2.0 mV/°C
- ► Maximum Vdiff is not a typically specified parameter in datasheets
- Other effects, like aging, are hard to predict

PDs will need a carefully designed input stage to control unbalance if a low power mode is needed. Use of diode rectifiers is probably not recommended if the PD must ensure a per pairset MPS.

MPS proposal

I _{Hold 2P}	Current the PSE must see on powered pairset(s) to consider MPS OK.
I _{Hold 4P}	Total current the PSE must see on both pairsets to consider MPS OK.
MPS both	PSE requires MPS to be met on both pairsets.
Sum/Max	Allowed MPS methods: sum-pairset and max-pairset
IPORT MPS/2P	Minimum current the PD must guarantee per powered pairset
IPort_MPS	Minimum total current the PD must guarantee
Timing	PSE or PD should follow the 'old' or 'new' timing

		PSE Requirements				PD Requirements		
PSE	PD	I _{Hold 2P}	I _{Hold 4P}	Timing	Sum/Max	IPORT_MPS /2P	I _{Port_MPS}	Timing
Туре 1,2	Type 1,2	5-10 mA	-	Old	-	-	10 mA	Old
	Type 3,4 Class \leq 4	5-10 mA	-	Old	-	-	10 mA	Old
	Type 3,4 Class \geq 5	5-10 mA	-	Old	-	-	10 mA	Old
	Type 3,4 2-channel	5-10 mA	-	Old	-	-	10 mA	Old
Type 3,4	Туре 1,2	-	5-10 mA	New	Yes	-	10 mA	Old
	Type 3,4 Class \leq 4	-	5-10 mA	New	Yes	-	10 mA	New
	Type 3,4 Class \geq 5	2-7 mA	-	New	Yes	7 mA	-	New
	Type 3,4 2-channel	2-7 mA	-	New	No	7 mA	-	New

Type 3/4 PSE MPS Rules

▶ PD Type 1, 2, 3[≤ Class 4]

- ► I_{Hold} = 5-10 mA, total current (no balance requirement)
- Support new MPS timings (6 ms / 354 ms)
- ► MPS methods: per-pairset, sum-pairset, max-pairset

▶ PD Type 3[≥ Class 5], Type 4

- ► I_{Hold} = 2-7 mA per pairset
- Support new MPS timings (6 ms / 354 ms)
- MPS methods: per-pairset, sum-pairset, max-pairset

PD Dual channel

- ► I_{Hold} = 2-7 mA per pairset
- Support new MPS timings (6 ms / 354 ms)
- MPS methods: per-pairset, sum-pairset, max-pairset

Type 3/4 PD MPS Rules

▶ PSE Type 1, 2

- I_{Port MPS} = 10 mA, total current (no balance requirement)
- Legacy timing: 75 ms / 250 ms

► PSE Type 3[≤ Class 4]

- I_{Port MPS} = 10 mA, total current (no balance requirement)
- New timing: 7 ms / 318 ms

PSE Type 3[> Class 5], Type 4

- I_{Port_MPS} = 7 mA, per pairset
- New timing: 7 ms / 318 ms

Balanced flexibility

The MPS rules in the previous slide are a balance between PSE and PD flexibility and allow a further reduction in standby power.

- Legacy Type 1/2 PDs cannot have any requirement imposed for unbalance at MPS currents.
- Since a PSE cannot distinguish the Type of a PD in classes 0-4, we can apply the legacy MPS rules (amplitude & balance) also to Type 3 PDs of class 0-4, without causing (extra) complications for the PSE.
- ► Type 3/4 single channel PDs in Class 5 or higher must present I_{Port_MPS} on both pair-sets.
- ► Type 3/4 PSEs may also look at the sum of currents or the highest current of both pairsets to consider MPS satisfied.
- Dual channel PDs must present I_{Port_MPS} on both pairsets

Conclusion

- ▶ Measurements of 720 diodes, 11 types, reveal Vdiff(max) < 35 mV
- Parallel diodes cannot be expected to have reliable current sharing behaviour at MPS level currents
- PDs should be able to implement diode rectifiers and support low standby
- This MPS proposal offers balanced design flexibility for PSE and PD
- Diode bridges are possible for Class 4 and below
- PDs without low power modes are not impacted by this unbalance issue

Propose for .bt group to adopt MPS rules in this presentation.





Diode equation

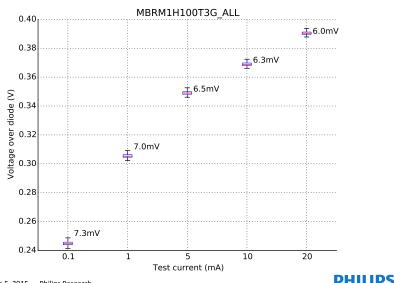
$$I = I_{s} \left(e^{\frac{qv}{nkT}} - 1 \right)$$
$$I_{s} = qA \frac{Dn_{i}^{2}}{LN_{D}} = qA \frac{D}{LN_{D}}BT^{3} \exp\left(-\frac{E_{G0}}{kT}\right)$$

Silicon diode voltage shifts by about $-2.5 \text{ mV/}^{\circ}\text{C}$ Schottky diode voltage shifts by about $-2.0 \text{ mV/}^{\circ}\text{C}$

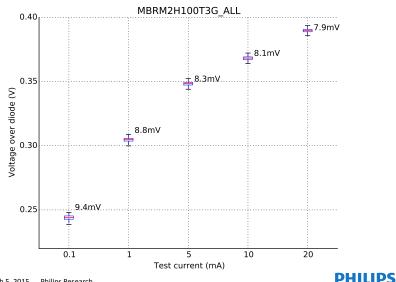
Reference: http://www.pveducation.org/pvcdrom/solar-cell-operation/ effect-of-temperature

17 March 5, 2015 Philips Research

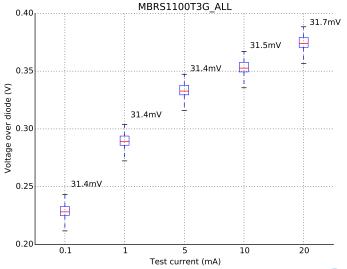
Diode measurement results: MBRM1H100T3GALL



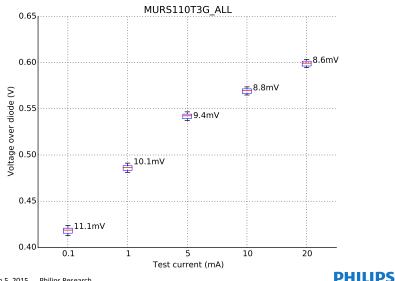
Diode measurement results: MBRM2H100T3GALL



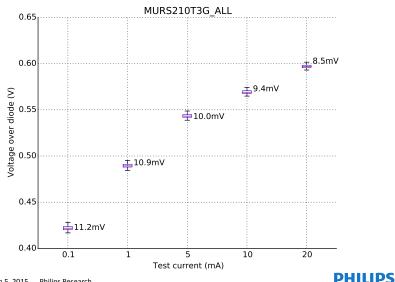
Diode measurement results: MBRS1100T3GALL



Diode measurement results: MURS110T3GALL



Diode measurement results: MURS210T3GALL



Diode measurement results: SS210ALL

